

Notice of References CitedApplication/Control No.
09/992,458Applicant(s)/Patent Under
Reexamination
SHIH ET AL.Examiner
Theresa T DoanArt Unit
2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-6,017,790	01-2000	Liou et al.	438/240
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	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	"High-K gate dielectrics: Current status and materials properties considerations", Journal of Applied physics; Volume 89, Number 10.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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